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BCY30, BCY31, BCY32, BCY33, BCY34
PNP Silicon Transistors JEDEC TO39 Package

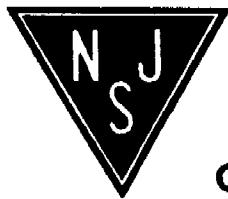
BCY30 series types are Silicon PNP Transistors manufactured by the epitaxial planar process for general purpose applications requiring lo gain (HFE) and low leakage

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

	<u>SYMBOL</u>	<u>BCY30</u>	<u>BCY31</u>	<u>BCY32</u>	<u>BCY33</u>	<u>BCY34</u>	<u>UNIT</u>
Collector-Base Voltage	V _{CBO}	64	64	64	32	32	V
Collector-Emitter Voltage	V _{C EV}	64	64	64	32	32	V
Emitter-Base Voltage	V _{EBO}	5.0	5.0	5.0	5.0	5.0	V
Collector Current	I _C			50			mA
Collector Current (Peak)	I _{CM}			100			mA
Base Current	I _B			15			mA
Base Current (Peak)	I _{BM}			50			mA
Power Dissipation	P _D			250			mW
Operating and Storage Junction Temperature	T _J , T _{STG}			-65 to +200			°C
Thermal Resistance	θ _{JA}			0.7			°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>BCY30</u>		<u>BCY31</u>		<u>BCY32</u>		<u>BCY33</u>		<u>BCY34</u>		<u>UNIT</u>
		<u>MIN</u>	<u>MAX</u>									
I _{CBO}	V _{CB} =6.0V		50		50		50		50		50	nA
I _{EBO}	V _{EB} =5.0V		50		50		50		50		50	nA
I _{EBO}	V _{EB} =6.0V, T _A =100°C	2.5		2.5		2.5		2.5		2.5		μA
BV _{CBO}	I _C =100μA	64		64		64		32		32		V
BV _{CEV}	I _C =100μA, V _{EB} =1.5V	64		64		64		32		32		V
BV _{EBO}	I _E =100μA	5.0		5.0		5.0		5.0		5.0		V
V _{CE(SAT)}	I _C =20mA, I _B =3.0mA	0.55		0.55		0.55		0.55		0.55		V
V _{BE(SAT)}	I _C =20mA, I _B =3.0mA	1.25		1.25		1.25		1.25		1.25		V
HFE	V _{CE} =4.5V, I _C =20mA	10	35	15	60	20	70	10	35	15	60	
f _T	V _{CE} =6.0V, I _C =1.0mA	1.0		1.0		1.0		1.0		1.0		MHz
C _{ob}	V _{CB} =6.0V, I _E =0, f=1.0MHz		60		60		60		60		60	pF
NF	V _{CE} =2.0V, I _E =0.5mA, R _g =500Ω, f=1.0kHz	20		20		20		20		20		dB



Quality Semi-Conductors